

Silicon PNP Power Transistors

2N6467 2N6468

DESCRIPTION

- With TO-66 package
- Excellent safe operating area
- Complement to type 2N6465 2N6466

APPLICATIONS

- For use in audio amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

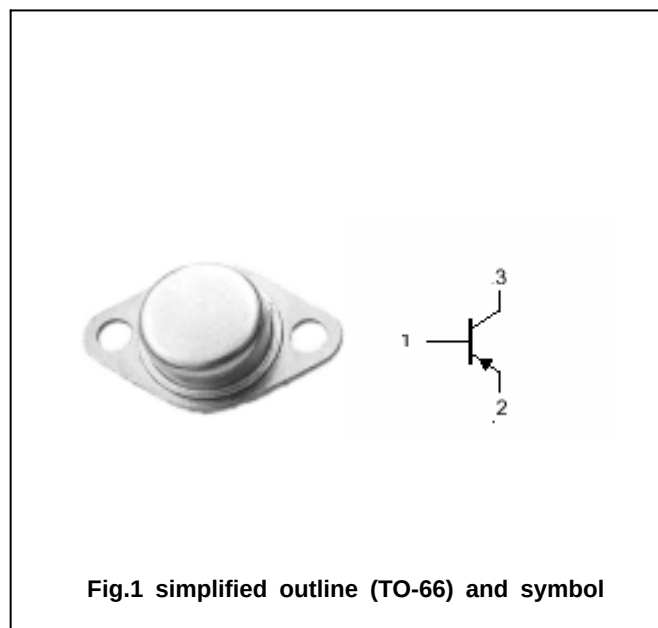


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings($T_a = ^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6467	Open emitter	-110	V
		2N6468		-130	
V_{CEO}	Collector-emitter voltage	2N6467	Open base	-100	V
		2N6468		-120	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-4	A
P_D	Total power dissipation		$T_C = 25^\circ\text{C}$	40	W
T_j	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	2.5	$^\circ\text{C/W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6467	I _C =-50mA ; I _B =0	-100			V
		2N6468		-120			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-1.5A; I _B =-0.15A			-1.2	V
V _{BE}	Base-emitter on voltage		I _C =-1.5A ; V _{CE} =-4V			-1.5	V
I _{CBO}	Collector cut-off current	2N6467	V _{CB} =-110V; I _E =0			-10	μA
		2N6468	V _{CB} =-130V; I _E =0				
I _{CEO}	Collector cut-off current	2N6467	V _{CE} = -100V, I _B =0			-100	μA
		2N6468	V _{CE} = -120V, I _B =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-10	μA
h _{FE}	DC current gain		I _C =-1.5A ; V _{CE} =-4V	15		150	
f _T	Transition frequency		I _C =-0.5A ; V _{CE} =-10V	5			MHz

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PACKAGE OUTLINE

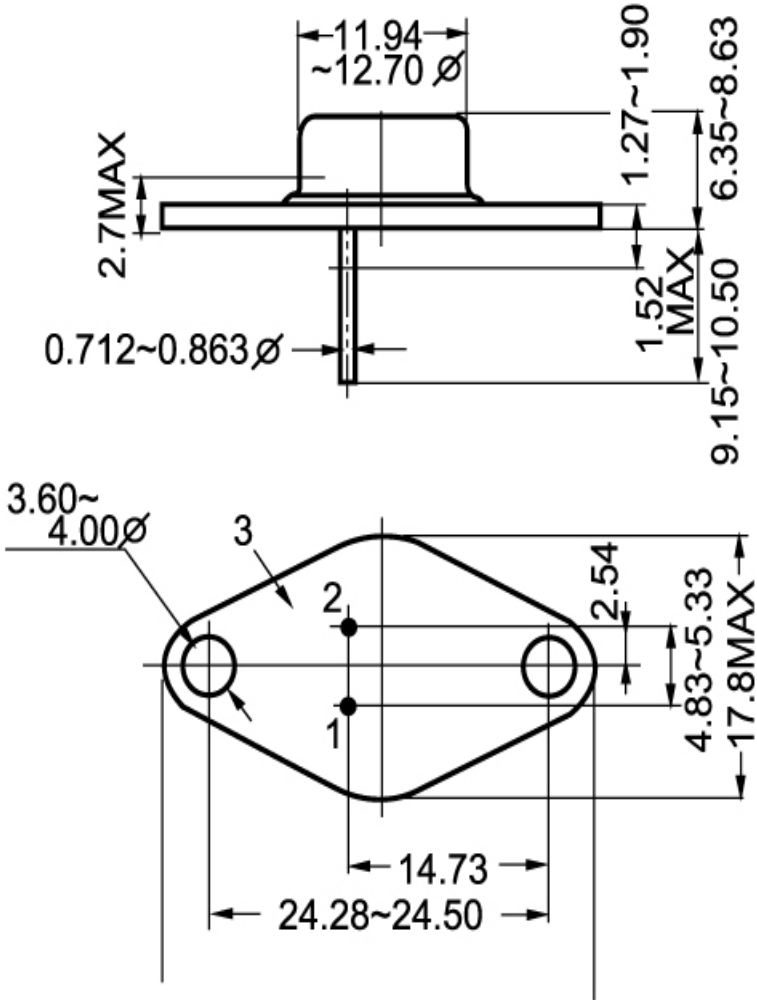


Fig.2 outline dimensions